

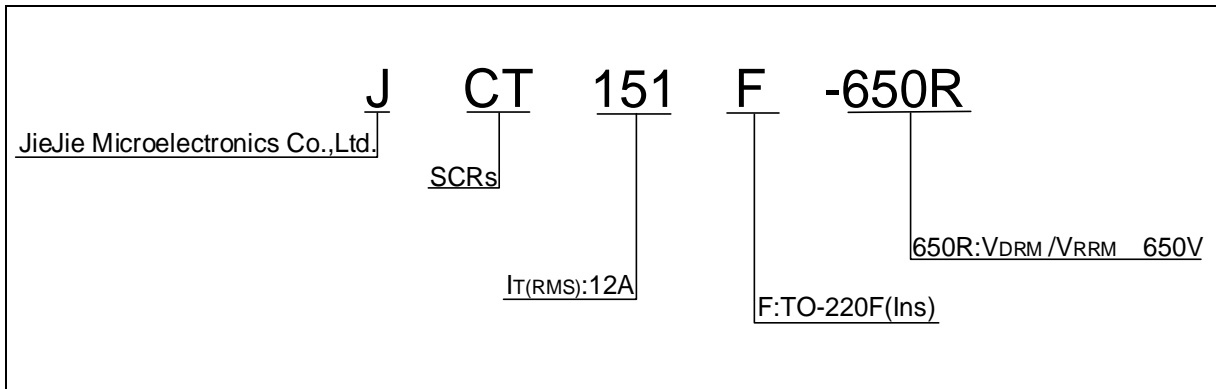
Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
D	$I_G=1.2I_{GT}$	-	-	40	mA

N = \hat{A} \hat{U} 5 I

ORDERING INFORMATION



MARKING

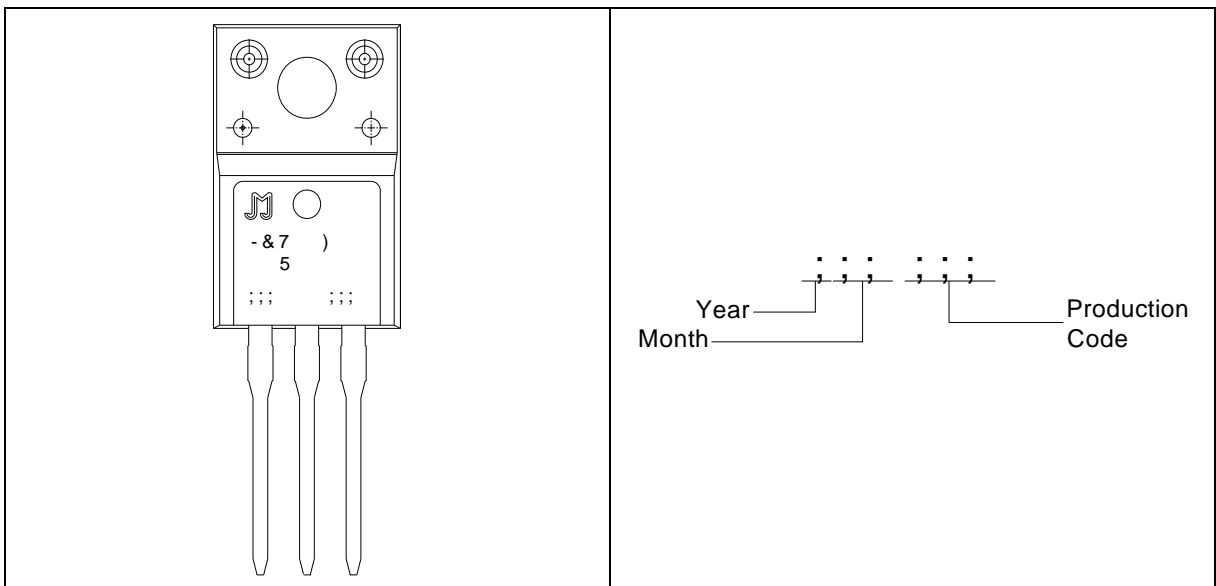
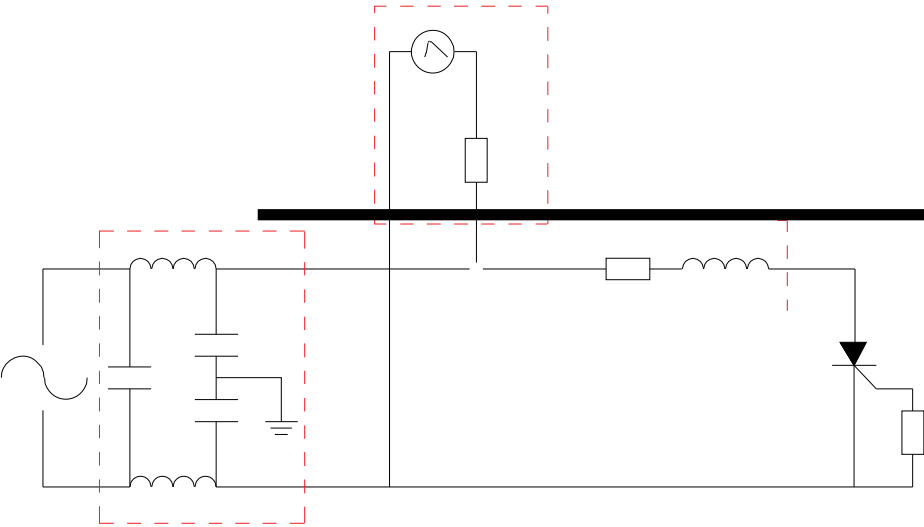


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT151F-650R	650	15	TO-220F(Ins)	50	Tube


Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Sept.28, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



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